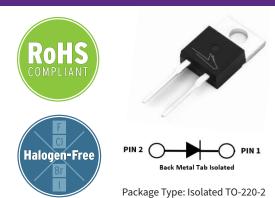


### 3rd Generation 650 V, 8 A Silicon Carbide Schottky Diode

#### **Description**

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



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Marking: C3D08065I

#### **Features**

- Low Forward Voltage (V<sub>F</sub>) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior
- Electrically Isolated Package (2.5kV)

### **Applications**

- Industrial Switched Mode Power Supplies
- Uninterruptible & AUX Power Supplies
- Boost for PFC & DC-DC Stages
- Solar Inverters
- AC/DC Converters

## **Maximum Ratings** (T<sub>c</sub> = 25°C Unless Otherwise Specified)

| Parameter                               | Symbol           | Value | Unit             | Test Conditions  | Notes  |  |
|---|------------------|-------|------------------|--|--------|--|
| Repetitive Peak Reverse Voltage         | V <sub>RRM</sub> | 650   |                  |  |        |  |
| DC Blocking Voltage                     | V <sub>DC</sub>  | 650   | V                |  |        |  |
|   |                  | 16.5  |                  | T <sub>c</sub> = 25 °C   |        |  |
| Continuous Forward Current              | I <sub>F</sub>   | 8     |                  | T <sub>c</sub> = 130 °C  | Fig. 3 |  |
|   |                  | 7.5   |                  | T <sub>c</sub> = 135 °C  | l      |  |
| Repetitive Peak Forward Surge           |                  | 29    |                  | $T_c = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}, \text{Half Sine Wave}$ |        |  |
| Current                                 | FRM              | 19    | А                | $T_c = 110 ^{\circ}\text{C}$ , $t_p = 10 \text{ms}$ , Half Sine Wave   |        |  |
| Non-Repetitive Forward Surge<br>Current | I <sub>FSM</sub> | 69    |                  | $T_c = 25$ °C, $t_p = 10$ ms, Half Sine Wave                           | Fig. 8 |  |
|   |                  | 55    |                  | $T_c = 110  ^{\circ}\text{C,t}_p = 10  \text{ms, Half Sine Wave}$      |        |  |
| Non-Repetitive Peak Forward             |                  | 650   |                  | $T_c = 25 ^{\circ}\text{C}, t_p = 10 \mu\text{s}, \text{Pulse}$        |        |  |
| Surge Current                           | F,Max            | 530   |                  | $T_{c} = 110^{\circ}\text{C}, t_{p} = 10 \mu\text{s}, \text{Pulse}$    |        |  |
| Power Dissipation                       | P <sub>tot</sub> | 53.6  | W                | T <sub>c</sub> = 25 °C   | Fig. 4 |  |
|   |                  | 23.2  |                  | T <sub>c</sub> = 110 °C  |        |  |
| Diode dV/dt ruggedness                  | dV/dt            | 200   | V/ns             | V <sub>R</sub> = 0-650V  |        |  |
| i²t value                               | ʃi²dt            | 23.8  | A <sup>2</sup> s | $T_c = 25  ^{\circ}\text{C}, t_p = 10  \text{ms}$                      |        |  |
|   |                  | 15    |                  | $T_{c} = 110^{\circ}C, t_{p} = 10 \text{ms}$                           |        |  |

#### **Electrical Characteristics**

| Parameter                 | Symbol         | Тур. | Max. | Unit | Test Conditions   | Notes  |
|---------------------------|----------------|------|------|------|---|--------|
| Famous ad Malda as        |                | 1.5  | 1.8  |      | I <sub>F</sub> = 8 A, T <sub>j</sub> = 25 °C                  | F:_ 1  |
| Forward Voltage           | V <sub>F</sub> | 2.1  | 2.4  | V    | I <sub>F</sub> = 8 A, T <sub>j</sub> = 175 °C                 | Fig. 1 |
| Reverse Current           |                | 10   | 51   | μА   | $V_R = 650 \text{ V}, T_j = 25 \text{ °C}$                    | Fig. 2 |
|                           | I <sub>R</sub> | 12   | 204  |      | $V_R = 650 \text{ V}, T_j = 175 \text{ °C}$                   |        |
| Total Capacitive Charge   | Q <sub>c</sub> | 20   |      | nC   | $V_R = 400 \text{ V}, T_j = 25 \text{ °C}, I_F = 8 \text{ A}$ | Fig. 5 |
|                           |                | 395  |      |      | $V_R = 0 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$   |        |
| Total Capacitance         | С              | 37   |      | pF   | $V_R = 200 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$ | Fig. 6 |
|                           |                | 32   |      |      | $V_R = 400 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$ |        |
| Capacitance Stored Energy | E <sub>c</sub> | 3.0  |      | μJ   | V <sub>R</sub> = 400 V  | Fig. 7 |

#### Notes:

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

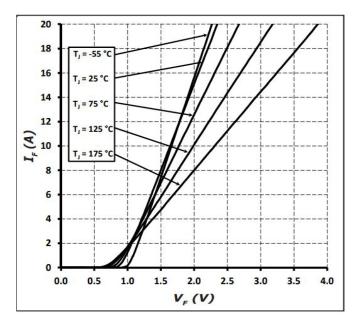
#### **Thermal & Mechanical Characteristics**

| Parameter                                      | Symbol                   | Value       | Unit   | Notes      |
|--|--------------------------|-------------|--------|------------|
| Thermal Resistance, Junction to Case (Typical) | R <sub>0, JC (TYP)</sub> | 2.8         | °C/W   |            |
| Junction Temperature                           | T <sub>j</sub>           | -55 to +175 | ۰,     |            |
| Case & Storage Temperature                     | T <sub>c</sub>           | -55 to +175 | °C     |            |
| TO 220 Mounting Toyana                         |                          | 1           | Nm     | M3 Screw   |
| TO-220 Mounting Torque                         | -                        | 8.8         | lbf-in | 6-32 Screw |

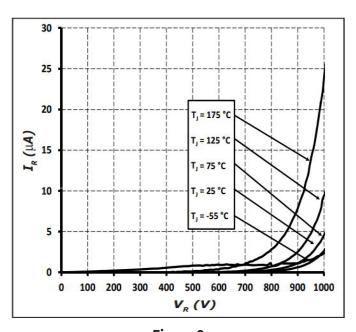
# **Electrostatic Discharge (ESD) Classifications**

| Parameter           | Symbol | Notes               |
|---------------------|--------|---------------------|
| Human Body Model    | НВМ    | Class 3B (≥ 8000 V) |
| Charge Device Model | CDM    | Class C3 (≥ 1000 V) |

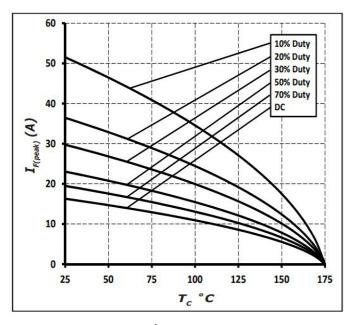
### **Typical Performance**



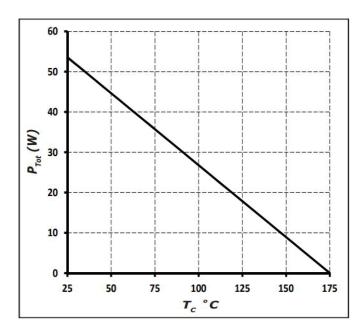
**Figure 1**Forward Characteristics



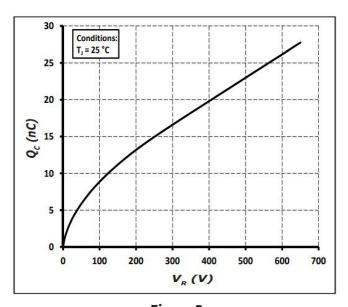
**Figure 2**Reverse Characteristics



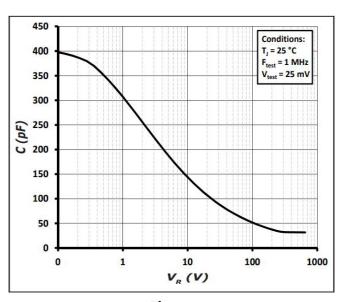
**Figure 3**Current Derating



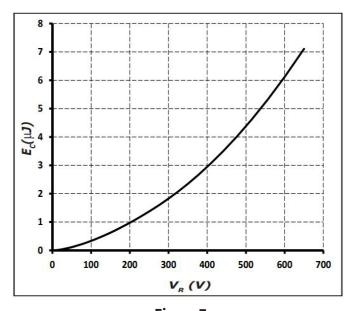
**Figure 4**Power Derating



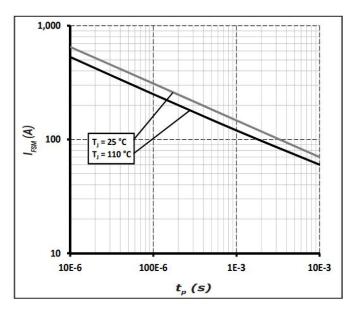
**Figure 5**Total Capacitance vs. Reverse Voltage



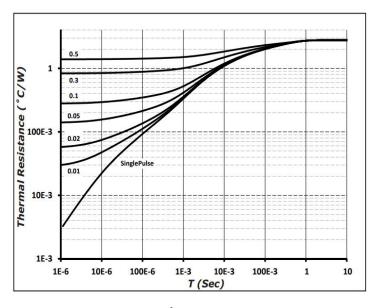
**Figure 6**Capacitace vs. Reverse Voltage



**Figure 7**Capacitance Stored Energy



**Figure 8**Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)



**Figure 9**Transient Thermal Impedance

### **Diode Model**

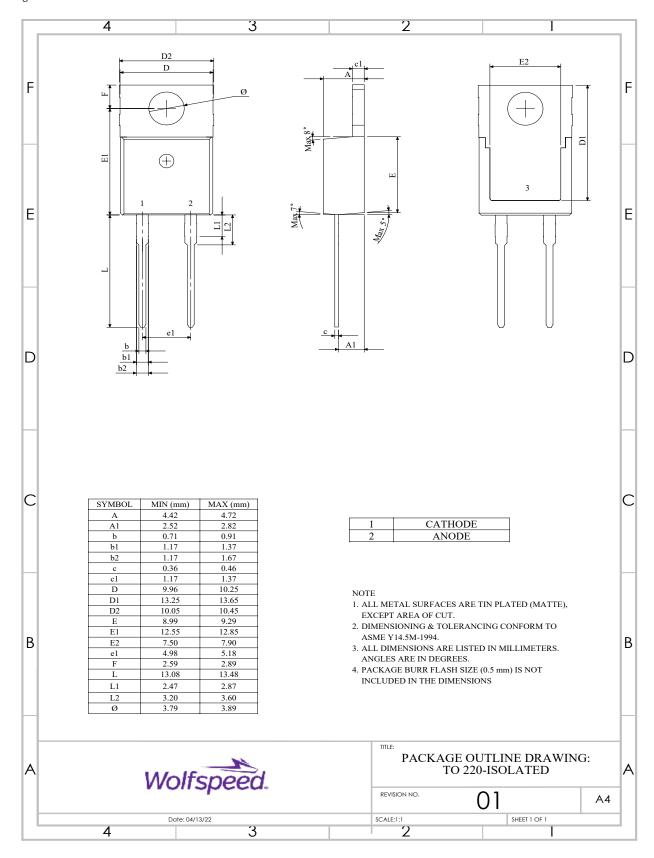
$$\begin{array}{c|c} - & & \\ \hline V_T & & R_T \\ \end{array}$$

$$Vf_T = V_T + If * R_T$$
 
$$V_T = 0.96 + (T_J * -1.1*10^{-3})$$
 
$$R_T = 0.07 + (T_J * 7.4*10^{-4})$$

Note: T<sub>j</sub> = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

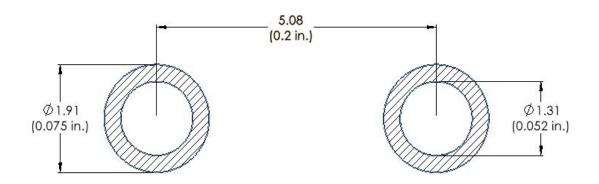
### **Package Dimensions & Pin-Out**

Package: TO-220-2



### **Recommended Solder Pad Layout**

Primary dimensions shown in mm.



# **Product Ordering Information**

| Order Number | Packing Type |  |
|--------------|--------------|--|
| C3D08065I    | Tube         |  |

# **Revision History**

| Document Version | Date of Release | Description of Changes                       |
|------------------|-----------------|--|
| С                | January-2018    | Initial Release                              |
| 5                | May-2023        | Update Package Drawing<br>Update Landing Pad |

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